

What is claimed is:

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1. A liquid crystal display device comprising:
a first substrate with a pixel area;
a first electrode pattern on the first substrate, wherein the first electrode pattern includes an edge;
an insulating layer over the first electrode pattern;
a second electrode pattern over the insulating layer, wherein the second electrode pattern includes at least two conductive members;
a short-prevention member on the insulating layer, above the edge, and between the at least two conductive members; and
a pixel electrode in the pixel area;
wherein the short-prevention member prevents electric shorts between the at least two conductive members caused by residual material that extends along the edge.
 2. The liquid crystal display device of claim 1, wherein the first electrode pattern includes a gate line, a gate electrode and a lower electrode of a storage capacitor.
 3. The liquid crystal display device of claim 1, wherein the second electrode pattern comprises a data line, a source electrode, a drain electrode and an upper electrode of a storage capacitor.
 4. The liquid crystal display device of claim 1, wherein the insulating layer forms a gate insulating layer.
 5. The liquid crystal display device of claim 4, further comprising:

a gate electrode under the gate insulating layer;
a semiconductor layer on the gate insulating layer and over the gate electrode; and
source and drain electrodes over the semiconductor layer.

5 6. The liquid crystal display device of claim 1, wherein the short-prevention member
is formed at a same time as the semiconductor layer.

7. The liquid crystal display device of claim 1, wherein the short-prevention member
is comprised of a same material as the semiconductor layer.

10 8. The liquid crystal display device of claim 1, further comprising:
a lower electrode; and
an upper electrode,
wherein the lower electrode and the upper electrode are separated by the insulating
15 layer.

9. The liquid crystal display device of claim 1, wherein the short-prevention member
is formed as an island.

20 10. The liquid crystal display device of claim 1, further including:
a second substrate adjacent the first substrate; and
a liquid crystal between the first substrate and the second substrate.

11. A liquid crystal display device comprising:
25 a gate pattern on a first substrate, the gate pattern including a gate line and a gate

electrode;

an insulating layer over the first substrate and the gate pattern;

a semiconductor layer on the insulating layer and over the gate electrode;

a short-prevention member on the insulating layer and over an edge of the gate

5 pattern;

a data pattern including a data line and source and drain electrodes,

a pixel electrode electrically connected to the drain electrode;

12. The liquid crystal display device of claim 11, wherein the gate electrode,
10 insulating layer, semiconductor layer, source/drain electrodes are parts of a thin film transistor.

13. The liquid crystal display device of claim 12, wherein the thin film transistor is
15 formed at a crossing of the gate line and the data line.

14. The liquid crystal display device of claim 13, wherein the short-prevention
member is formed at a same time as the semiconductor layer.

15. The liquid crystal display device of claim 14, wherein the short-prevention
20 member is formed of a same material as the semiconductor layer.

16. The liquid crystal display device of claim 11, further comprising a storage
capacitor, wherein the gate line forms a lower electrode and wherein the data pattern further
forms an upper electrode, of the storage capacitor.

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17. The liquid crystal display device of claim 11, wherein the short-prevention member is an island.

18. The liquid crystal display device of claim 11, further including:

5 a second substrate adjacent the first substrate; and

a liquid crystal layer between the first and second substrates.

19. A method of fabricating a liquid crystal display device, comprising:

forming a first electrode pattern on a first substrate having a pixel area;

10 forming an insulating layer over the first substrate and over the first electrode pattern;

forming a short-prevention member on the insulating layer and over an edge of the first electrode pattern;

forming a second electrode pattern on the insulating layer; and

15 forming a pixel electrode in the pixel area;

wherein the short-prevention member is disposed to prevent electric shorts in the second electrode pattern.

20 20. The method of claim 19, wherein the first electrode pattern is formed using a wet etch process, and wherein the first electrode pattern includes a gate line, a gate electrode, and a lower electrode of a storage capacitor

25 21. The method of claim 19, wherein the second electrode pattern is formed using a wet etch process, and wherein the second electrode pattern includes a data line, source/drain electrodes, and an upper electrode of a storage capacitor.

22. The method of claim 20, further comprising:
forming a gate electrode under the insulating layer;
forming a semiconductor layer over the insulating layer; and
forming source/drain electrodes over the semiconductor layer.

23. The method of claim 22, wherein the short-prevention member is formed of a
same material as the semiconductor layer.

24. The method of claim 19, wherein the short-prevention member is formed as an
island.

25. The method of claim 19, wherein the short-prevention layer is formed by dry
etching.

26. A method of fabricating a liquid crystal display device, comprising:
forming a gate pattern on a first substrate, wherein the gate pattern includes a gate
line, a gate electrode, and a lower electrode;
forming an insulating layer over the first substrate and over the gate pattern;
forming a semiconductor layer on the insulating layer and over the gate electrode,
forming a short-prevention member on the insulating layer and over an edge of the
gate pattern;
forming a data pattern, including a data line, source/drain electrodes, and an upper
electrode; and
forming a pixel electrode having an electrical connection to the drain electrode.

27. The method of claim 26, wherein the short-prevention member is formed of a same material as the semiconductor layer.

28. The method of claim 26, wherein the short-prevention member is formed as an island.

29. The method of claim 26, wherein the gate pattern is formed using a wet etch process.

30. The method of claim 26, wherein the data pattern is formed using a wet etch process.

31. The method of claim 26, wherein the semiconductor layer and short-prevention member are each formed using a dry etch process.

32. The method of claim 26, further including disposing a second substrate adjacent the first substrate.

33. The method of claim 26, further including disposing a liquid crystal between the first substrate and the second substrate.